

MOSFETs Silicon N-Channel MOS ( $\pi$ -MOSVII)

# TK40J20D

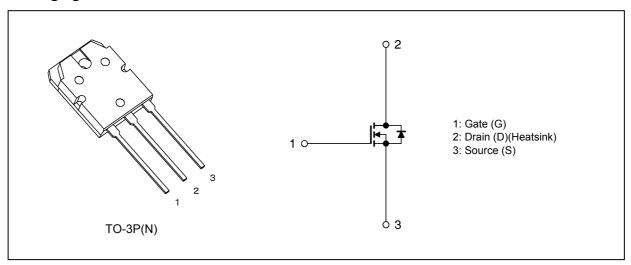
#### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.0374 \Omega$  (typ.)
- (2) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 200 \text{ V)}$
- (3) Enhancement mode:  $V_{th} = 1.5 \text{ to } 3.5 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA})$

#### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	200	٧
Gate-source voltage		V <sub>GSS</sub>	±20	
Drain current (DC)	(Note 1)	I <sub>D</sub>	40	Α
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	160	
Power dissipation (T <sub>c</sub> = 25°C)		$P_{D}$	260	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	435	mJ
Avalanche current	(Note 3)	I <sub>AR</sub>	40	Α
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	40	
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	160	
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



#### 5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	0.481	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	50	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 50 V,  $T_{ch}$  = 25°C (initial), L = 0.43 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 40 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



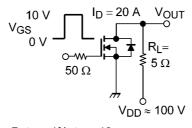
#### 6. Electrical Characteristics

### 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	_	±1	μА
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	200	_	_	V
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.5	_	3.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	1	0.0374	0.044	Ω

#### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	4300	_	pF
Reverse transfer capacitance	C <sub>rss</sub>			30		
Output capacitance	C <sub>oss</sub>		_	280		
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN, f = 1 MHz	1	5.2		Ω
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.		100		ns
Switching time (turn-on time)	t <sub>on</sub>		_	160		
Switching time (fall time)	t <sub>f</sub>		_	85	_	
Switching time (turn-off time)	t <sub>off</sub>		_	510		



Duty  $\leq$  1%,  $t_W$  = 10  $\mu s$ 

Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 160 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 40 \text{ A}$	_	100	_	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	17	_	
Gate-drain charge	Q <sub>gd</sub>		_	33	_	

### 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	$V_{DSF}$	I <sub>DR</sub> = 40 A, V <sub>GS</sub> = 0 V		1	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 40 A, V <sub>GS</sub> = 0 V		240		ns
Reverse recovery charge	$Q_{rr}$	-dl <sub>DR</sub> /dt = 100 A/μs		2.2		μС
Peak reverse recovery current	I <sub>rr</sub>			18		Α



### 7. Marking (Note)

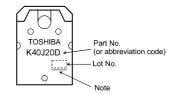


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS

compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the

restriction of the use of certain hazardous substances in electrical and electronic equipment.

## 8. Characteristics Curves (Note)

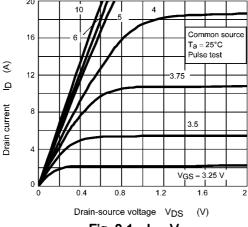


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

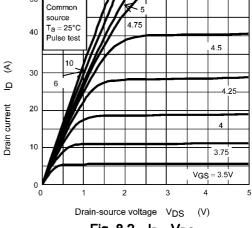


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

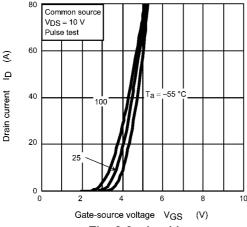


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

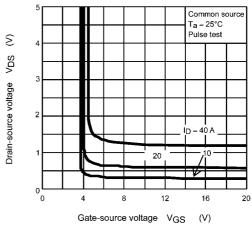


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

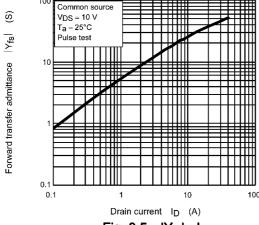


Fig. 8.5 |Y<sub>fs</sub>| - I<sub>D</sub>

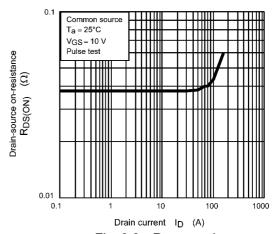


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>

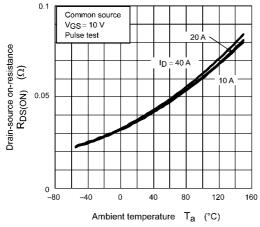


Fig. 8.7  $R_{DS(ON)}$  -  $T_a$ 

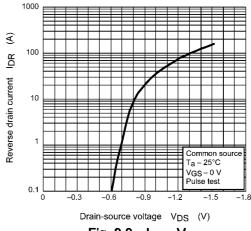


Fig. 8.8 I<sub>DR</sub> - V<sub>DS</sub>

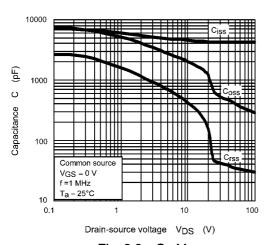


Fig. 8.9 C - V<sub>DS</sub>

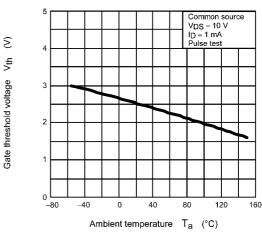


Fig. 8.10 V<sub>th</sub> - T<sub>a</sub>

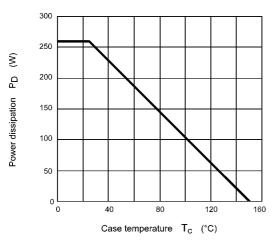


Fig. 8.11 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

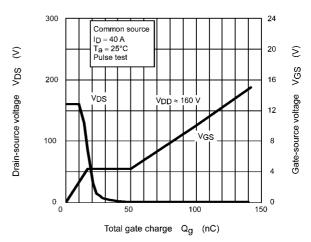


Fig. 8.12 Dynamic Input/Output Characteristics

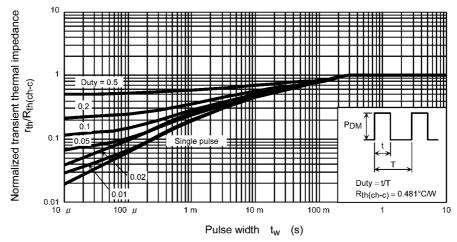


Fig. 8.13  $r_{th}/R_{th(ch-c)} - t_w$  (Guaranteed Maximum)

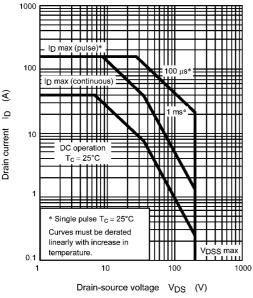


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

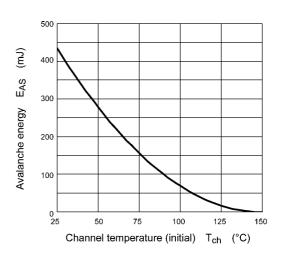


Fig. 8.15 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

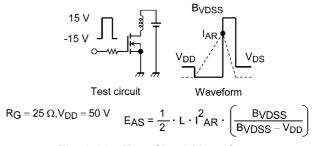


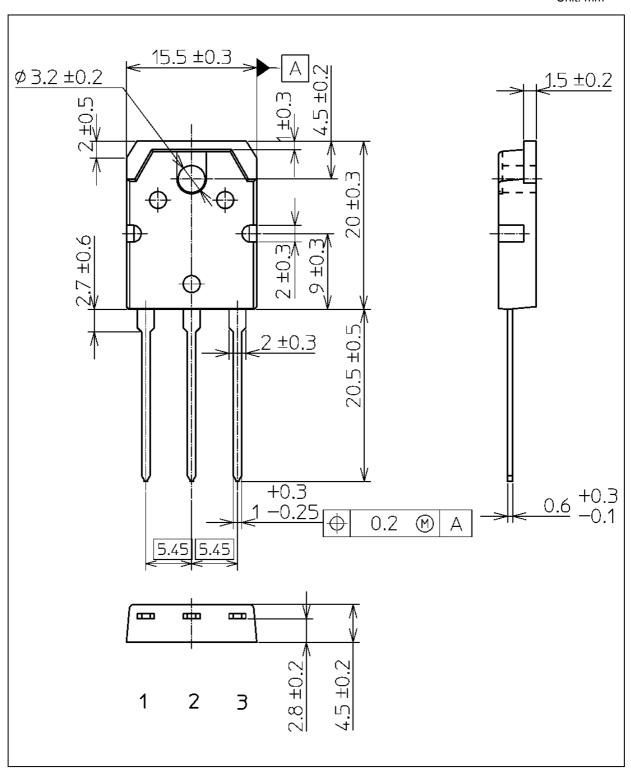
Fig. 8.16 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 4.6 g (typ.)

	Package Name(s)
JEITA: SC-65	
TOSHIBA: 2-16C1S	
Nickname: TO-3P(N)	



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